



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Lin, et al. Docket No.: TSM02-1369
Serial No.: 10/650,445 Art Unit: 2811
Filed: August 28, 2003 Examiner: TBD
For: Ultra-Thin Body Transistor with Recessed Silicide Contacts

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Date of Deposit: March 17, 2004

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Certificate of Mailing via First Class Mail (1 page)
Information Disclosure Statement (1 page)
Combined Form PTO/SB/08a and 08b (1 page) citing (6) references
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Respectfully submitted,

Natalie Swider
Legal Assistant

Slater & Matsil, L.L.P.
17950 Preston Rd., Suite 1000
Dallas, TX 75252
Tel: 972-732-1001
Fax: 972-732-9218



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Commissioner for Patents
P. O. Box 1450
Alexandria, VA 22313-1450

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Applicants wish to bring to the attention of the Patent and Trademark Office the information noted on the enclosed combined form PTO/SB/08a & 08b that may be considered material to the examination of the above-identified application.

No fee is due at this time, as this Information Disclosure Statement is being filed pursuant to 37 C.F.R. § 1.97(b)(3), before the mailing of a first Office action on the merits. However, if a fee is deemed necessary, please charge Deposit Account No. 50-1065 and credit any overpayments to the same.

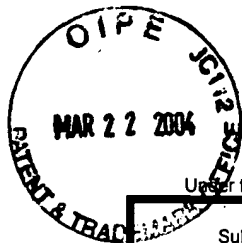
Respectfully submitted,

Steven H. Slater
Attorney for Applicants
Reg. No. 35,361

March 17, 2004

Date

Slater & Matsil, L.L.P.
17950 Preston Rd., Suite 1000
Dallas, TX 75252
(972) 732-1001 (phone)
(972) 732-9218 (fax)



Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

Complete if Known

Application Number	10/650,445
Filing Date	8/28/2003
First Named Inventor	Lin, et al.
Art Unit	2811
Examiner Name	TBD
Attorney Docket Number	TSM02-1369

Sheet 1 of 1

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code ² (if known)			
	1	US-4,998,510	03-12-1991	Rognon	
	2	US-6,137,149	10-24-2000	Kodama	
	3	US-6,420,218 B1	07-16-2002	Yu	

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ - Number ⁴ - Kind Code ⁵ (if known)				

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
	4	Chau, R., et al., "A 50nm Depleted-Substrate CMOS Transistor (DST)," IEDM, pp. 621-624, 2001.	
	5	Choi, Y.K., et al., "Ultrathin-Body SOI MOSFET for Deep-Sub-Tenth Micron Era," IEEE Electron Device Letters, Vol. 21, No. 5, pp. 254-255, May 2000.	
	6	Yeo, Y.C., et al., "Design and Fabrication of 50-nm Thin-Body p-MOSFETs with a SiGe Heterostructure Channel," IEEE Transactions on Electron Devices, Vol. 49, No. 2, pp. 279-286, February 2002.	

Examiner Signature		Date Considered	
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. ²Applicant's unique citation designation number (optional). ³See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ⁴Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁵For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁶Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁷Applicant is to place a check mark here if English language translation is attached.

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